



Bipolar PNP Bare Die – BTP180

Part Description

The BTP180 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

Key Parameters:

- VCBO = -40V
- VCEO = -40V
- VEBO = -5V
- hFE = 40-120 @ VCE = -1V, IC = -0.5A
- VCE(Sat) = -1V @ IC = -1A, IB = -100mA
- fT = - MHz @ VCE = - V, IE = - A
- COBO = - pF @ VCB = - V

Features

Designed to provide performance equivalent to 2N3467

Die Size (Unawn)

760 μ m X 760 μ m, 30 Mils X 30 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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